

#### Using MLC NAND in Datacenters

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#### Abstract



SSDs are typically constructed using SLC as the datacenter NAND technology. Primarily because of the endurance and write performance of SLC NAND. For many usages, MLC NAND is more cost effective and can support the endurance and write performance required by the end user. This course outlines the different NAND usages in datacenter and highlights how MLC is a cost effective solution for datacenter applications.

#### Learning Objectives

- Understand tradeoffs for SLC NAND versus MLC NAND in datacenter
- Understand how for specific applications MLC NAND is more cost effective
- Understand how to tune MLC NAND to your application needs



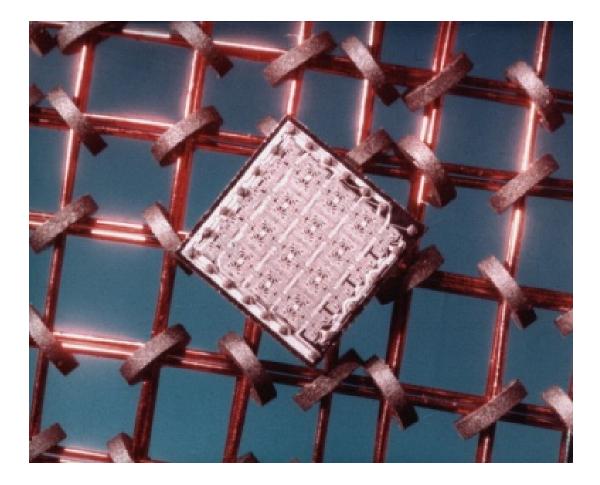


#### Basics of NAND technology

- Basics of datacenter workloads
- MLC datacenter SSD
- Workload Examples

### **Question: What is the picture?**



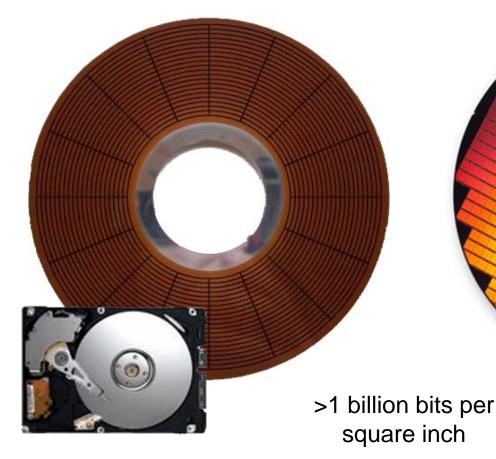


#### Integrated circuit foreground, core memory background

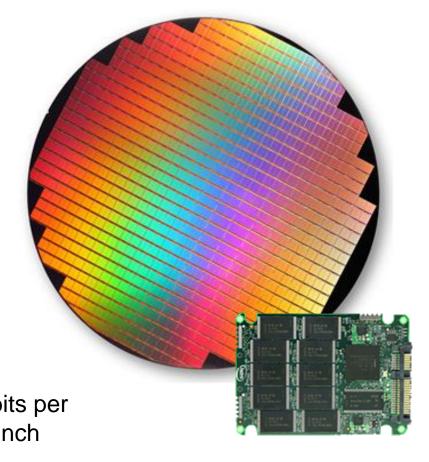
### NAND...



Hard Disk Drive Platter record data by directionally magnetizing ferromagnetic material



<u>NAND Silicon</u> records data by "flashing" electron charges in an array of floating-gate transistors





#### NAND Block

	Page 63		→
	Page 62		
	Page 61		
			- 256⊧
	Page 3		
	Page 2		
	Page 1		
Sector 7	Page 0	Sector 0	
		512 bytes	
	γ	)	
	4K bytes		

SSD NAND is arrange as blocks, pages, and sectors

- 256K bytes



#### NAND Block

101110	101110	101110	101110
	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110

- NAND sector/page is write once
- NAND sector/page is read many

Valid Data

Invalid Data



#### NAND Block

101110	101110	101110	101110
	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110

- NAND sector/page is write once
- NAND sector/page is read many
- When a NAND page is "full" and "aged", the page is first cleared, unused and cleared NAND creates in write-amp (WA)
- and then erased

- Valid Data
- Invalid Data



#### NAND Block

101110	101110	101110	101110
	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110
101110	101110	101110	101110



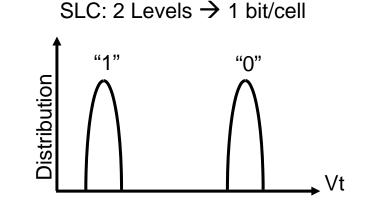
- NAND sector/page is read many
- When a NAND page is "full" and "aged", the page is first cleared, unused and cleared NAND creates in write-amp (WA)
- and then erased
- Each block erase is a cycle

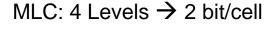
Valid Data

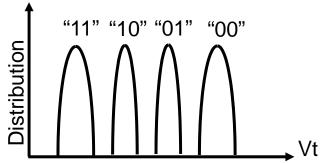
Invalid Data

### NAND SLC, MLC, etc

- Single Level Cell (SLC): 2 voltage levels
  - Level 0 = Erased = 0
  - Level 1 = Programmed = 1
- Multi-Level Cell (MLC): 4 voltage levels
  - Level 0 = Erased = 0
  - Level 1 = Programmed to L1 = 01
  - Level 2 = Programmed to L2 = 10
  - Level 3 = Programmed to L3 = 11
- Others
  - 2.5 bits per cell: 6 voltage levels
  - 3 bits per cell: 8 voltage levels
  - 4 bits per cell: 16 voltage levels



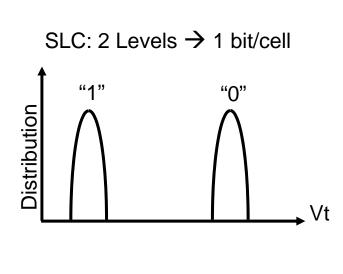






<b>Typical Specification</b>	SLC	MLC
Bits per Cell	I	2
Page Size (K)	4	4
Pages/Block	64	128
Page Program (us)	250	900
Random Read (us)	25	50
Block Erase (ms)	2	2
Typical Program/ Erase Cycles	100,000	10,000

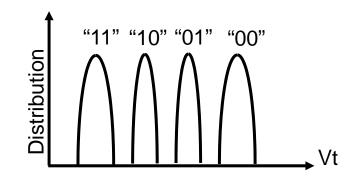
Highlighted specs affect ROI for SSD use in datacenter.



Education

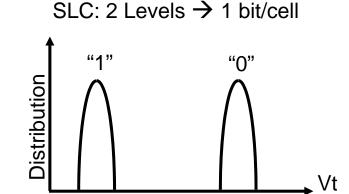
SNII

MLC: 4 Levels  $\rightarrow$  2 bit/cell



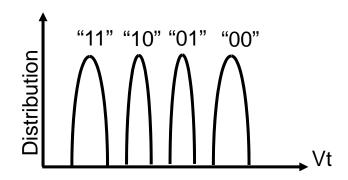
### **SLC & MLC Endurance/Lifetime**

- JDEC shelf life 1 year
  - SLC 100,000 cycles
  - MLC 10,000 cycles
- Program/Erase Cycle
  - NAND block clear
  - Write amplification
- Bottom Line It depends
  - Controller design
  - Firmware design
  - Usage Case



Education





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### **What Impacts Endurance?**

NAND Technology erase cycles (SLC vs MLC ) Write Workload Random vs Sequential Spare Area Capacity reserve / work space

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#### Managed by:

Firmware Algorithms

Efficiency of NAND writes (Write amplification) and wearleveling

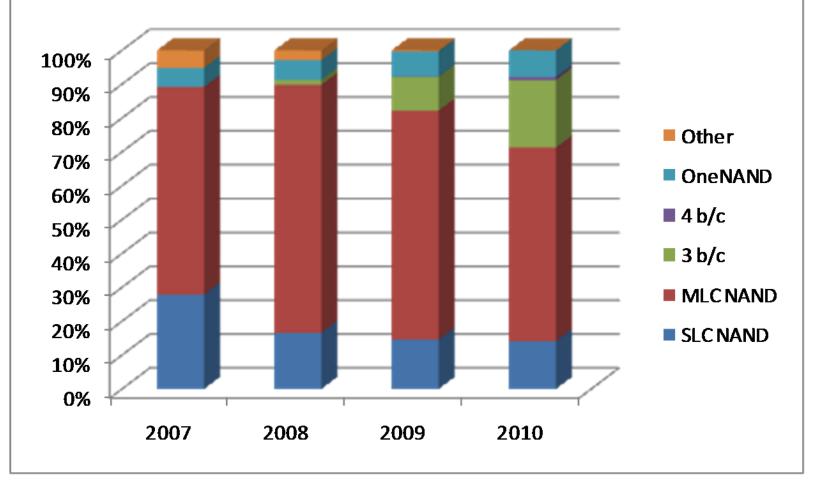
#### **Delivers**:

Drive Endurance Drive design and arch matters!

Lower write amplification → Fewer NAND cycles → Faster write perf High Random Writes = Endurance Efficiency

## **SLC / MLC**

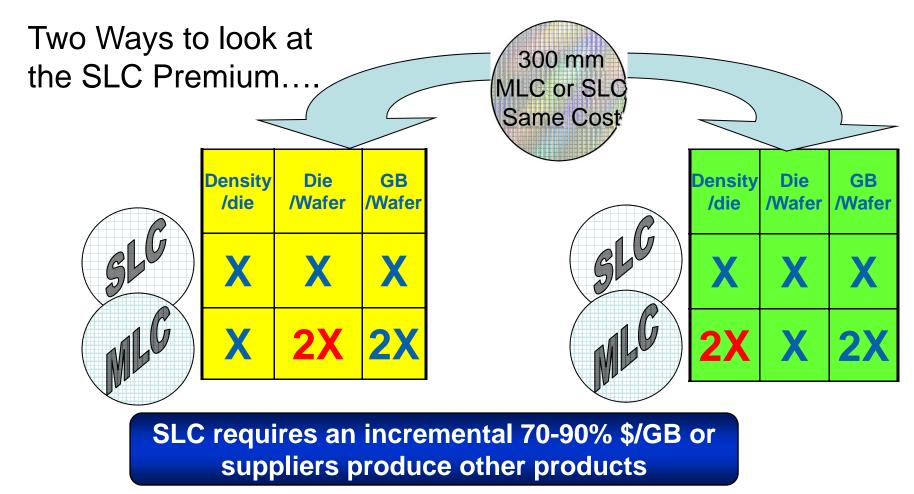




#### NAND moving to greater charges per cell. Greater capacity at the expense of endurance and write speed



#### **Choice of MLC vs SLC at Given Density**



\*Showing worst case for SLC - Actual MLC / SLC Delta ~ 80-90% assuming optimizations, timing issues, etc.





#### Basics of NAND technology

#### Basics of datacenter workloads

- MLC datacenter SSD
- Workload Examples

### **Legacy Storage in the Datacenter**



	Contraction Contraction				
		_			
Storage Usage	Central Storage		Caching/ Proximity Tier		Server Attached
Cache	Local DRAM cache: (e.g. OS block, hot application data)	,	<b>DRAM cache:</b> (Memcached, Storage virtualization appliance)	,	<b>Local DRAM cache:</b> (HDD Block Cache, Database Cache, NFS v4 cache)
Boot	Local boot data: (SAN/NAS image)	Fabric (FC and	<b>Local boot:</b> (Appliance image)	Fabric (FC and	Local boot data when not Pixie: (Operating System, Hypervisor, SWAP, VM, Application Image)
Performance	Hot Application Data (Database, Email, etc)	GE/I0GE)		GE/I0GE)	Hot Application Data (Web, Database, Email, Search, Videos, etc)
Capacity	<b>Cold/Luke-warm</b> <b>Application Data</b> (Data warehouse, Documents, Backups, Archive, etc)				Luke-warm Application Data (Web, Email, Videos, etc)

### **Emerging NAND** in the Datacenter



	Terrent Terrent Terrent				
Storage Usage	Central Storage		Caching/ Proximity Tier		Server/Workstation Attached
Cache (\$/IOPS, Latency)	LBA Cache: SAS/PCIe SSDs (SLC)	Fabric	LBA and Data Cache: SAS/SATA/PCIe SSD (SLC)	Fabr	LBA Cache: SATA SSD (SLC)
Boot (\$/GB)	Local Boot Data: SAS/SATA SSD (MLC/3BC)	(FC and G	Local Boot Data: SSD (MLC/3BC)	Fabric (FC and G	Local Boot Data when not PXE: SATA/SATA SSD (MLC/3BC)
Performance (\$/IOP/GB)	Hot Application Data SAS SSDs (MLC)	E/I0GE)		and GE/I0GE)	Hot Application Data SATA SSDs (MLC)
Capacity (\$/TB, (TB)	Cold/Luke-warm Application Data SATA HDDs (future SSD 3BC/4BC?)	nter		. ind	Luke-warm Application Data SATA HDDs (future SSD 3BC/4BC?)

### **The ROI Basics – SNIA TCO Calculator**



#### For 3.5TB business intelligence database

I46G I5K SAS drives (SNIA default data)

			_	4K - 8K	16K - 32K	64K - 128K
	What is the I/O transfer size in KB?	8K	example:	OS,	Large File Transfer	Video Streaming
2	Which of the following most closely characterizes your application's I/O?	65/35	%reads/%writes	Transactions	Earger ne manarer	video Sireaning
For questic	ons 3 - 11, input information about your current Hard Drive confi	iguration.	_			
3	Select your current HDD size	2.5 Inch				
4	Select your HDD storage interface	SAS				
5	Select your current HDD RPM	15K rpm				
6	Select your current HDD per unit raw capacity	146 GB				
7	How many Hard Drives do you currently have in the application?	24	]			
8	What percentage of your Hard Drive capacity is consumed?	100%	(Include headroom if	needed)		
9	What RAID configuration do you currently use?	No Raid	]			
10	Do you currently purchase maintenance plans for your hard drives?	no	]			
11	How many instances (or systems) of the above configuration do you have?	1	]			

#### • 64G SLC drives (<u>www.newegg.com</u> 3/21/10 pricing)

тсо	I/O Performance	IOPS	Reduction in power	Previous	Total	Total HDD	Total Usable
Impact	Improvement	Gain		HDD Total	SSS	Consumed	SSS Capacity
(\$40,948)	2554%	285,150	58.3%	24	55	3504 GB	3520 GB

#### 60G MLC drives (<u>www.newegg.com</u> 3/21/10 pricing)

тсо	I/O Performance	IOPS	Reduction in power	Previous	Total	Total HDD	Total Usable
Impact	Improvement	Gain		HDD Total	SSS	Consumed	SSS Capacity
\$57	663%	73,984	81.8%	24	24	3504 GB	3523 GB

#### SNIA CO Calculator: <u>www.snia.org/forums/sssi/programs/TCOcalc/</u>

Using MLC NAND in Datacenter Applications

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Basics of NAND technology

Basics of datacenter workloads

#### MLC datacenter SSD

Workload Examples

### **Nuances of SSD Performance/Endurance**

### I. Type of NAND

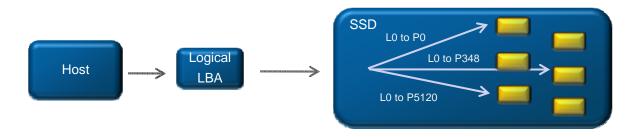
- Single Level Cell (SLC)
- Multi Level Cell (MLC)
- Others (2.5BC, 3BC, etc)
- 2. Indirection system
  - Erasing and Writing Blocks
- 3. Host traffic pattern
  - Workload and Fullness of SSD
- 4. Spare area
  - SSD Workspace
- 5. Power off shelf life

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#### Nuance of the "Indirection System"



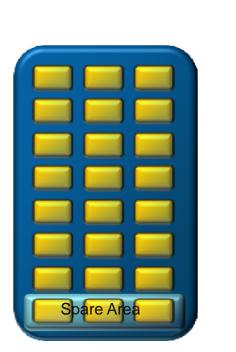
- Logical to physical LBA mapping removes need for atomic operations like read modify write (RMW)
  - The placement of new LBA information can be packed into pages that are at new physical locations
- Data placement in previously erased blocks makes foreground work (Host IO operations) faster
- Indirection "clean up" needs to reclaim invalid physical locations in background



SSD converts a Physical Page to Logical LBA. Logical LBA will not reside in the same physical location each time it is written

#### **Host Traffic Pattern: Empty vs Full**





Sequential data

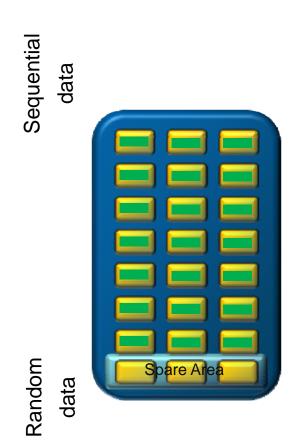
- An empty SSDs achieves its maximum write performance under all workloads
- Once initially filled performance will decrease
- Study State write performance is achieved when the SSD has settled into a consistent write latencies pattern
- A Steady State can be observed when
  - User capacity is full
  - Consistent work load is provided

SSDs steady state performance will have dependencies on

the amount of spare area

#### **Host Traffic Pattern: Sequential vs Random**





- Steady state performance of an SSD full of sequential data is better than the steady state of an SSD full of random data
  - Sequential sectors will be invalidated in larger linear clusters than random.
  - Invalidation of sectors within a block is spotty in random writes.
- Changing the workload of an SSD from sequential to random will cause the performance to fall whereas changing from random to sequential will increase performance over time.

#### Less erase cycles on the blocks as we do less background data

increasing the available "ready to be written" resource

- SLC already maximizes spare area
- Increase MLC Performance by

Larger work space allows

movement

<> □

pool

- Factory option Set Max LBA to decrease user capacity and increase Spare Area
- User option Define a partition less than the max available capacity
- Increasing spare capacity can boost performance by 10% or more.
  The main benefit it allows for more consistent performance.

#### **Spare Area: The Transitory Working Space**

Increasing the Spare Area helps performance by

for less data movement to reclaim blocks.

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Less background data movement increases performance



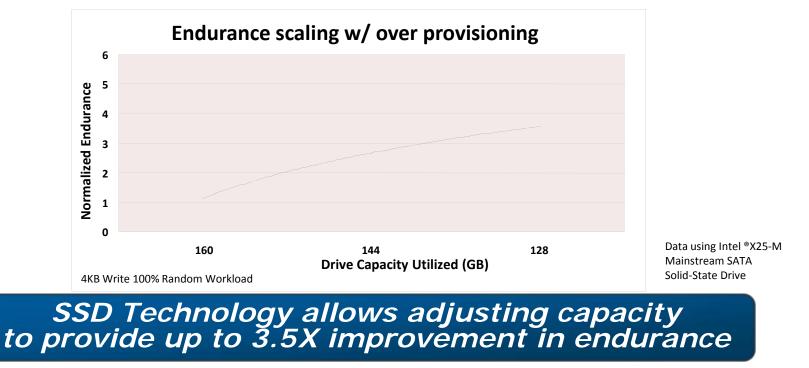


### **Spare Area Affects Endurance**



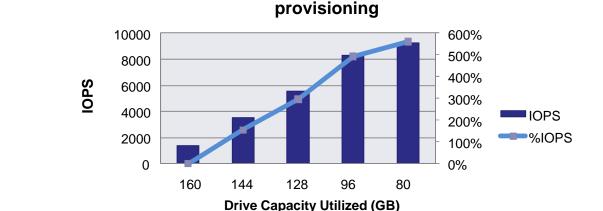
Increasing spare area increases endurance

- Spare area beyond 27% of native capacity has diminishing returns
- Adjust SSD spare area by limiting drive capacity
  - ATA8-ACS Host Protected Area feature set is used (SET MAX ADDRESS)
  - Use ATA8-ACS SECURITY ERASE UNIT prior to limiting capacity
  - Setting partition to smaller size after erase is an option (less robust)



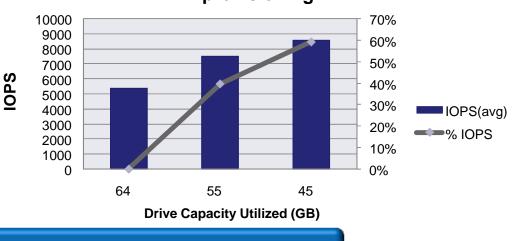
## **Drive Performance vs Spare Area**





160GB MLC Performance scaling w/ over

#### 64GB SLC Performance scaling w/ over provisioning



#### As spare area increases so does performance

MLC has a greater % performance increase due to the relative smaller spare area to start with

Data using Intel <sup>®</sup>X25-M Mainstream SATA and Intel<sup>®</sup> X25-E Extreme SATA Solid-State Drives





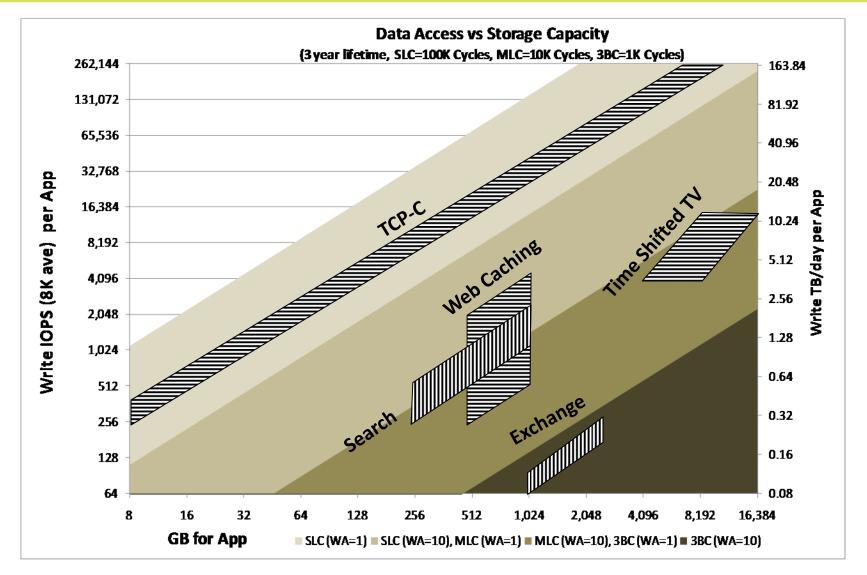


Basics of NAND technology

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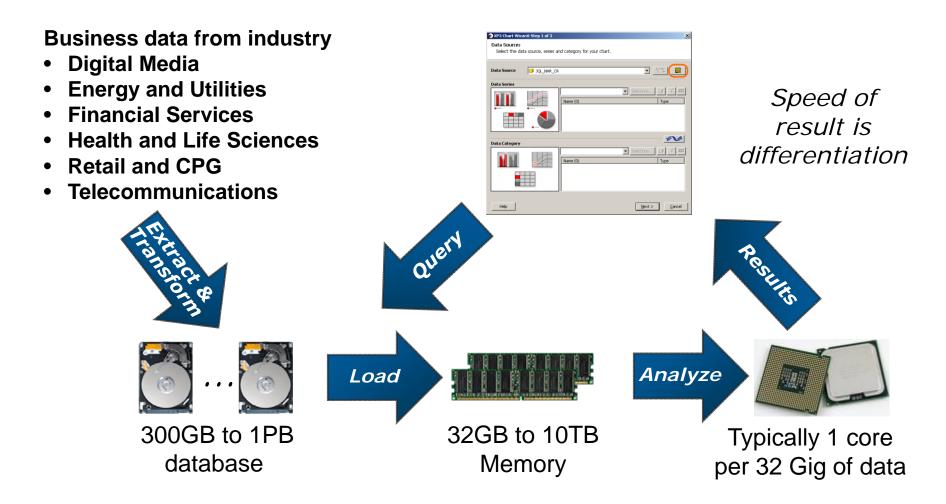
### **Mapping workloads to NAND**





## **Business Intelligence: Example**



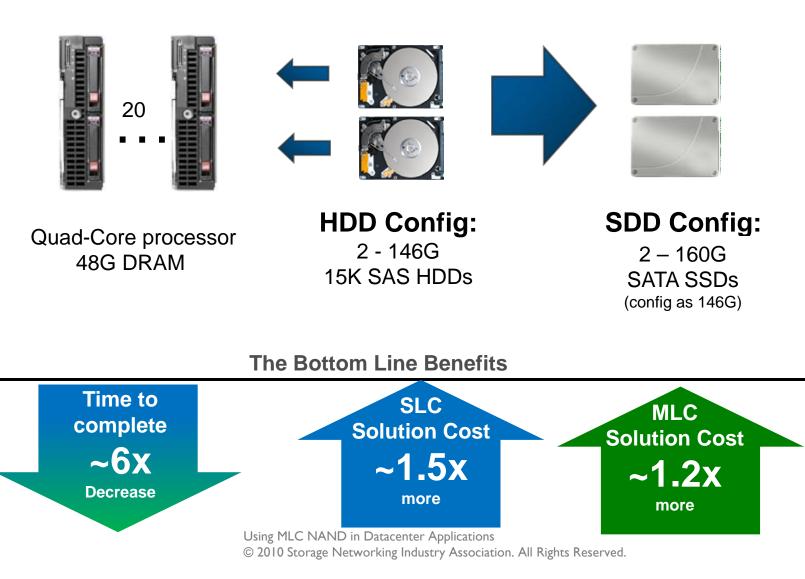


### **Business Intelligence:**



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Financial services example



### Summary



- Best ROI achieve by focusing on solution
- MLC today for most application solutions meets
  - Endurance/Lifetime needs
  - Read/Write performance needs
- MLC cost today (and likely in future)
  - Significantly better than 2x less in \$/G



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Many thanks to the following individuals for their contributions to this tutorial. - SNIA Education Committee

**Tony Roug**